FH3055GS

N-Channel Enhancement Mode MOSFET

Description

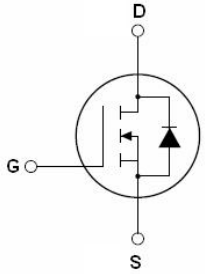
The FH3055GS is the N-Channel enhancementmode MOSFET in a plastic package (PDFN5x6-8L) using the Trench technology.

Applications

- High Speed Switch
- DC-DC Converters
- Lithium-Ion Battery

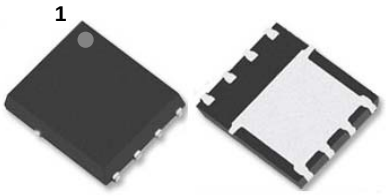
Features

- V_{DS} = 30V ; I_D = 65A
  $R_{DS(ON)}$(Typ.)= 4.2mΩ @V_{GS} = 10 V
  $R_{DS(ON)}$(Typ.)= 6.5mΩ @V_{GS} = 4.5V
- LogicLevelCompatible
- SMDPackage(PDFN5x6-8L)
- TrenchTechnology
- FastSwitching



Schematic diagram

Marking and pin Assignment



PDFN5x6-8L top and bottom view

Absolute Maximum Ratings (T_A = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	T_C = 25 ℃	30	-	V
V_{GS}	Gate-Source Voltage	T_C = 25 ℃	-	± 20	V
I_D*	Drain Current (DC)	T_C = 25 ℃, V_{GS} = 10 V	-	65	A
		T_C = 100 ℃, V_{GS} = 10 V	-	44	A
I_{DM}*,**,***	Drain Current (Pulsed)	T_C = 25 ℃, V_{GS} = 10 V	-	223	A
P_{tot}*	Total Power Dissipation	T_C = 25 ℃	-	35	W
T_{stg}	Storage Temperature		-55	150	℃
T_J	Junction Temperature		-	150	℃
I_S	Diode Forward Current	T_C = 25 ℃	-	65	A
E_{AS}*	Single Pulsed Avalanche Energy	V_{DD}= 30 V , L= 1 mH	-	117	mJ
$R_{\theta JA}$*	Thermal Resistance- Junction to Ambient		-	62.5	℃ / W
$R_{\theta JC}$*	Thermal Resistance- Junction to Case		-	3.5	

Notes :

* Surface Mounted on 1 in^2 pad area, t ≤ 10 sec

** Pulse width ≤ 300 μs, duty cycle ≤ 2 %

*** limited by bonding wire

Electrical Characteristics (T_A = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	30	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_{DS} = 250 µA	1	-	2	V
I_{DSS}	Zero Gate Voltage Source Current	V_{DS} = 24 V, V_{GS} = 0 V	-	-	1	µA
I_{GSS}	Gate Leakage Current	V_{GS} = ± 20 V, V_{DS} = 0 V	-	-	± 100	nA
$R_{DS(ON)}$[a]	Drain-Source On-State Resistance	V_{GS} = 10 V, I_D = 15 A	-	4.2	5.2	mΩ
		V_{GS} = 4.5 V, I_D = 10A	-	6.5	8.7	
Diode Characteristics						
V_{SD}[a]	Diode Forward Voltage	I_{SD} = 15 A, V_{GS} = 0 V	-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_{SD} = 15 A, dI_{SD}/dt = 100 A/µs	-	14	-	nS
Q_{rr}	Reverse Recovery Charge		-	3.3	-	nC
Dynamic Characteristics[b]						
C_{iss}	Input Capacitance	V_{GS} = 0 V, V_{DS} = 15 V Frequency = 1 MHz	-	960	-	pF
C_{oss}	Output Capacitance		-	238	-	
C_{rss}	Reverse Transfer Capacitance		-	69	-	
t_d(on)	Turn-on Delay Time	V_{DS} = 15 V, V_{GEN} = 10 V, R_G = 3.9 Ω, R_L = 1 Ω, I_{DS} = 15 A	-	6.7	-	nS
t_r	Turn-on Rise Time		-	41	-	
t_d(off)	Turn-off Delay Time		-	26	-	
t_f	Turn-off Fall Time		-	19	-	
Gate Charge Characteristics[b]						
Q_g	Total Gate Charge	V_{DS} = 15 V, V_{GS} = 10 V, I_{DS} = 15 A	-	21	-	nC
Q_{gs}	Gate-Source Charge		-	4.3	-	
Q_{gd}	Gate-Drain Charge		-	4.7	-	

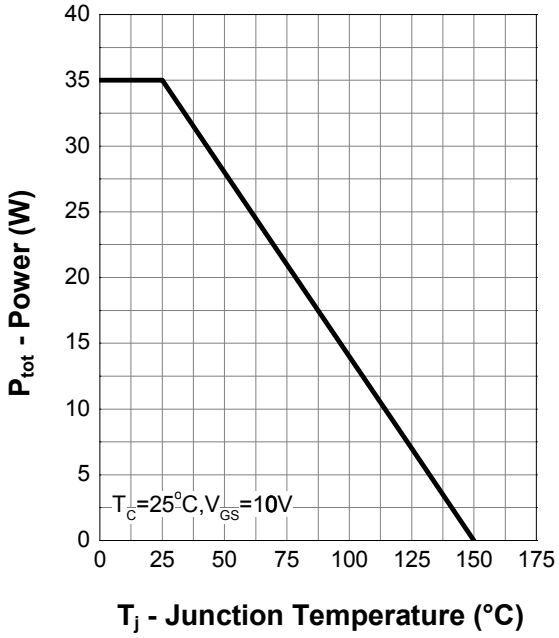
Notes1 :

a : Pulse test ; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b : Guaranteed by design, not subject to production testing

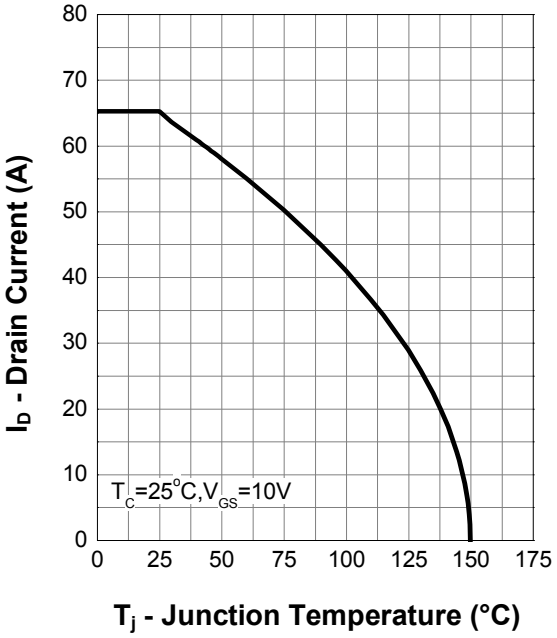
Note2: NHCX defines " Green " as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

Typical Characteristics (Cont.)

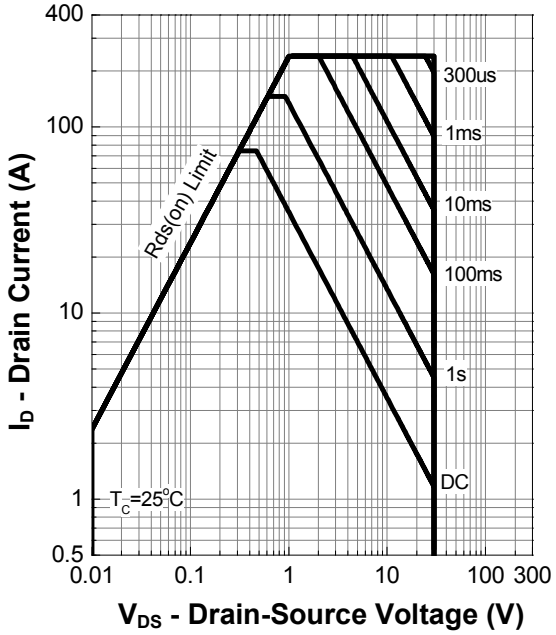
Power Capability



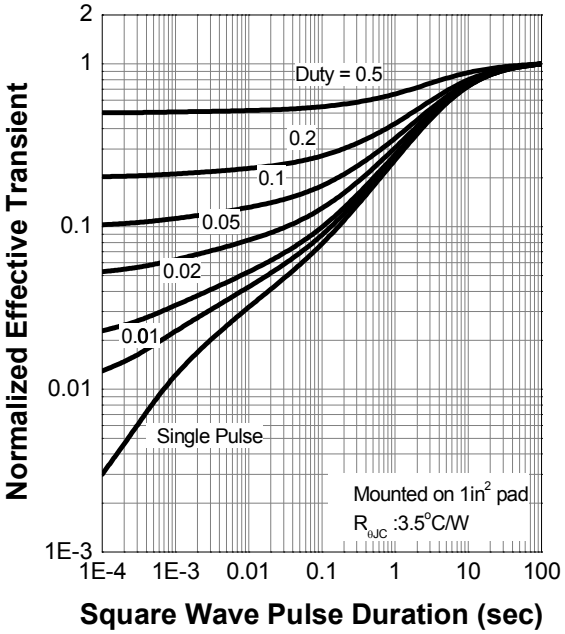
Current Capability



Safe Operation Area

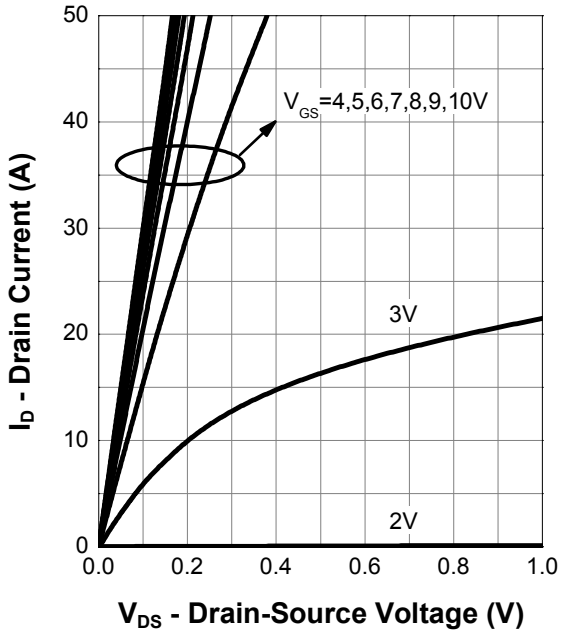


Transient Thermal Impedance

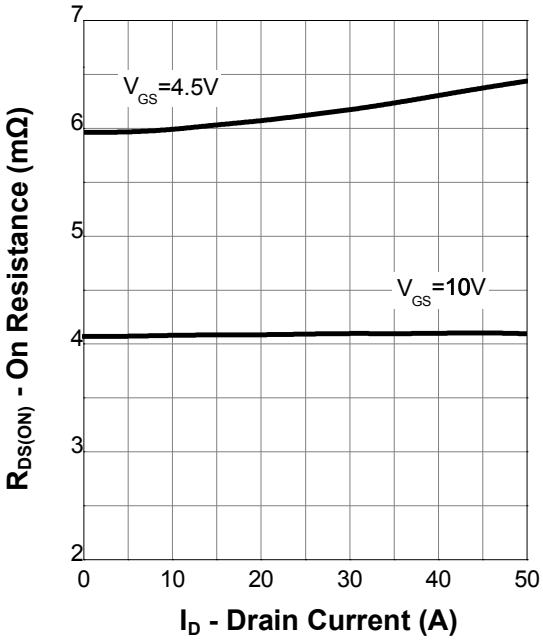


Typical Characteristics (Cont.)

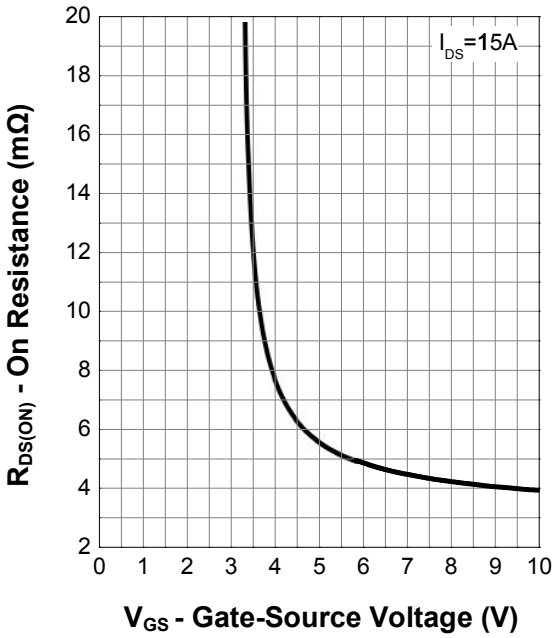
Output Characteristics



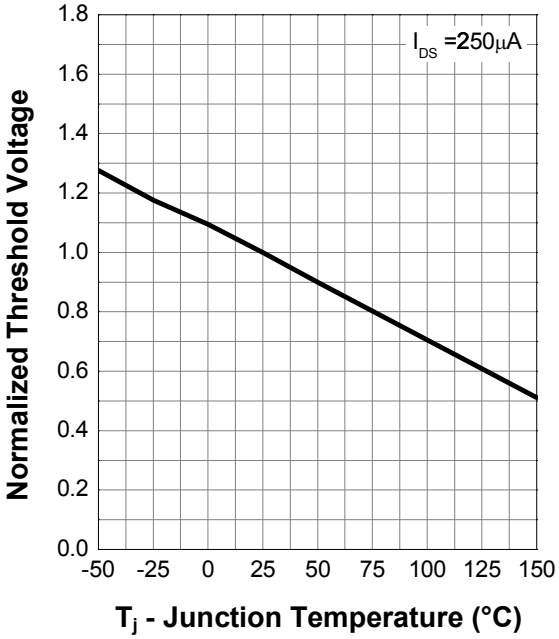
On Resistance



Transfer Characteristics

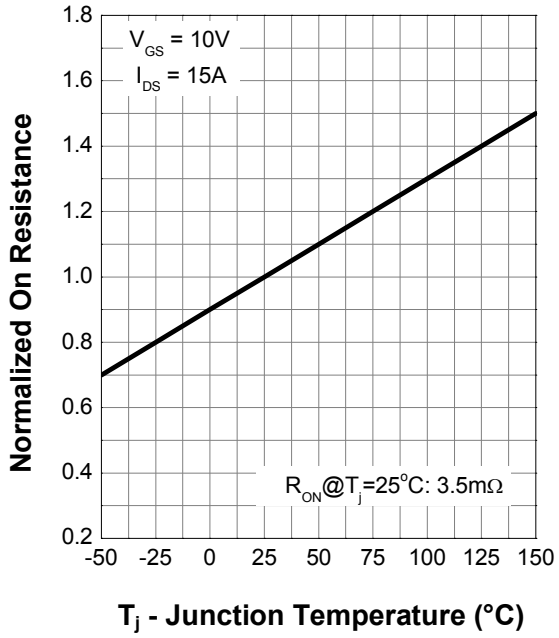


Normalized Threshold Voltage

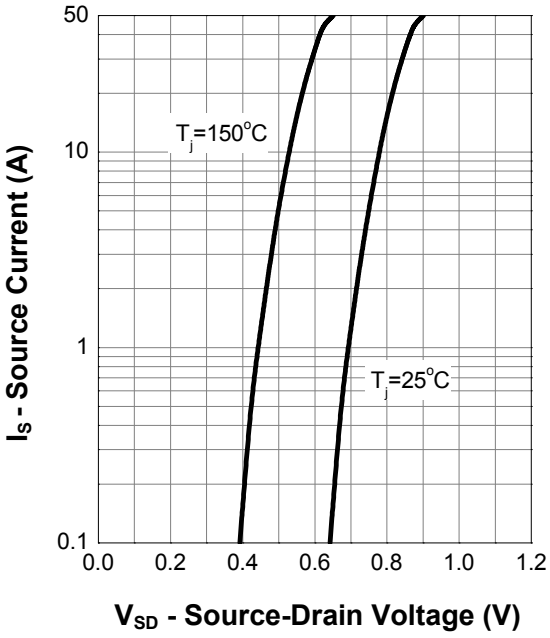


Typical Characteristics (Cont.)

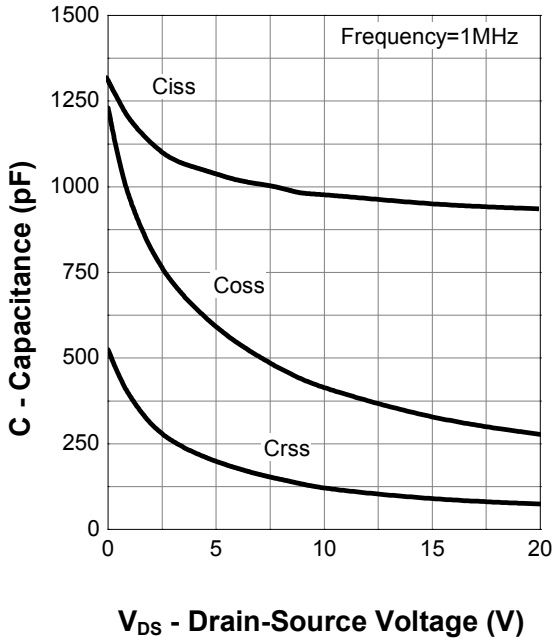
Normalized On Resistance



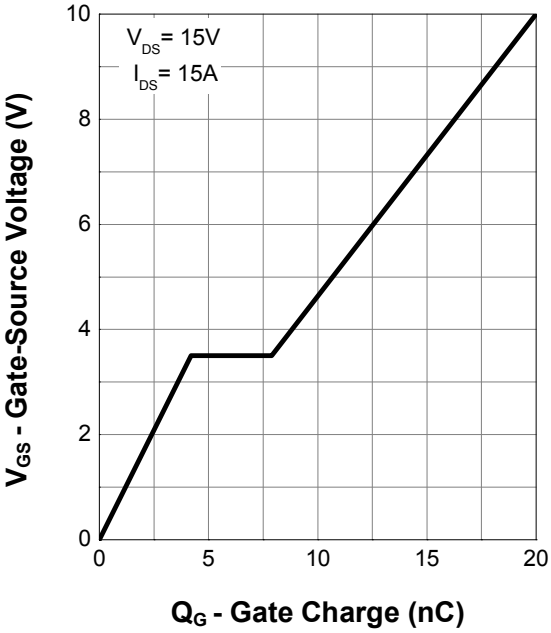
Diode Forward Current



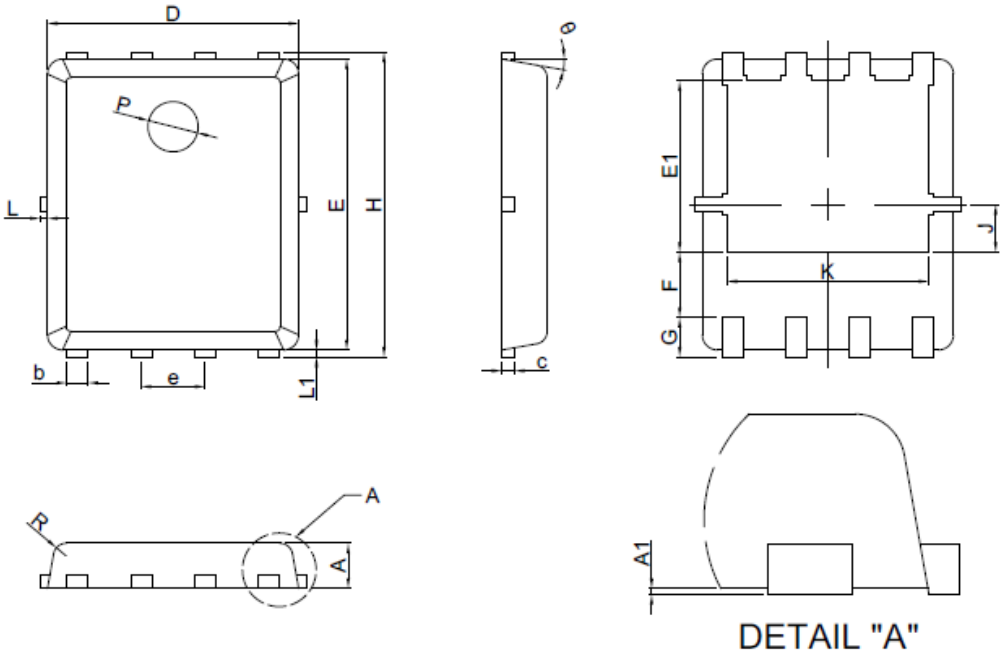
Capacitance



Gate Charge



Package Information：PDFN5x6-8L



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.80	1.00
A1	0.00	0.05
b	0.35	0.49
c	0.254REF	
D	4.80	5.20
F	1.40REF	
E	5.60	5.90
e	1.27BSC	
H	5.80	6.20
L1	0.10	0.18
G	0.60REF	
K	4.00REF	
L	-	0.15
J	0.95BSC	
P	1.00REF	
E1	3.40REF	
θ	6°	14°
R	0.25REF	